

Christophe Durand

List of Publications by Year in Descending Order

Source: <https://exaly.com/author-pdf/4795414/christophe-durand-publications-by-year.pdf>

Version: 2024-04-24

This document has been generated based on the publications and citations recorded by exaly.com. For the latest version of this publication list, visit the link given above.

The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

28

papers

1,282

citations

16

h-index

29

g-index

29

ext. papers

1,395

ext. citations

5.6

avg, IF

3.85

L-index

#	Paper	IF	Citations
28	Dual-Color Emission from Monolithic m-Plane Core-Shell InGaN/GaN Quantum Wells. <i>Advanced Photonics Research</i> , 2021 , 2, 2000148	1.9	1
27	Self-powered proton detectors based on GaN core-shell p-n microwires. <i>Applied Physics Letters</i> , 2021 , 118, 193501	3.4	1
26	Stretchable Transparent Light-Emitting Diodes Based on InGaN/GaN Quantum Well Microwires and Carbon Nanotube Films. <i>Nanomaterials</i> , 2021 , 11,	5.4	2
25	Carrier dynamics near a crack in GaN microwires with AlGaIn multiple quantum wells. <i>Applied Physics Letters</i> , 2020 , 117, 221105	3.4	4
24	Role of Underlayer for Efficient Core-Shell InGaN QWs Grown on -plane GaN Wire Sidewalls. <i>ACS Applied Materials & Interfaces</i> , 2020 , 12, 19092-19101	9.5	12
23	UV Emission from GaN Wires with -Plane Core-Shell GaN/AlGaIn Multiple Quantum Wells. <i>ACS Applied Materials & Interfaces</i> , 2020 , 12, 44007-44016	9.5	7
22	Colour optimization of phosphor-converted flexible nitride nanowire white light emitting diodes. <i>JPhys Photonics</i> , 2019 , 1, 035003	2.5	3
21	Radiation sensors based on GaN microwires. <i>Journal Physics D: Applied Physics</i> , 2018 , 51, 175105	3	6
20	Green Electroluminescence from Radial m-Plane InGaN Quantum Wells Grown on GaN Wire Sidewalls by Metal-Organic Vapor Phase Epitaxy. <i>ACS Photonics</i> , 2018 , 5, 4330-4337	6.3	18
19	Thin-Wall GaN/InAlN Multiple Quantum Well Tubes. <i>Nano Letters</i> , 2017 , 17, 3347-3355	11.5	9
18	Comprehensive analyses of core-shell InGaN/GaN single nanowire photodiodes. <i>Journal Physics D: Applied Physics</i> , 2017 , 50, 484001	3	12
17	Flexible White Light Emitting Diodes Based on Nitride Nanowires and Nanophosphors. <i>ACS Photonics</i> , 2016 , 3, 597-603	6.3	72
16	InGaN/GaN core/shell nanowires for visible to ultraviolet range photodetection. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2016 , 213, 936-940	1.6	15
15	Multi-microscopy study of the influence of stacking faults and three-dimensional In distribution on the optical properties of m-plane InGaN quantum wells grown on microwire sidewalls. <i>Applied Physics Letters</i> , 2016 , 108, 042102	3.4	23
14	Flexible Photodiodes Based on Nitride Core/Shell p-n Junction Nanowires. <i>ACS Applied Materials & Interfaces</i> , 2016 , 8, 26198-26206	9.5	52
13	Investigation of Photovoltaic Properties of Single Core-Shell GaN/InGaN Wires. <i>ACS Applied Materials & Interfaces</i> , 2015 , 7, 21898-906	9.5	32
12	Flexible Light-Emitting Diodes Based on Vertical Nitride Nanowires. <i>Nano Letters</i> , 2015 , 15, 6958-64	11.5	149

11	M-Plane GaN/InAlN Multiple Quantum Wells in CoreShell Wire Structure for UV Emission. <i>ACS Photonics</i> , 2014 , 1, 38-46	6.3	37
10	Integrated photonic platform based on InGaN/GaN nanowire emitters and detectors. <i>Nano Letters</i> , 2014 , 14, 3515-20	11.5	148
9	Correlation of microphotoluminescence spectroscopy, scanning transmission electron microscopy, and atom probe tomography on a single nano-object containing an InGaN/GaN multiquantum well system. <i>Nano Letters</i> , 2014 , 14, 107-14	11.5	63
8	Experimental and theoretical analysis of transport properties of core-shell wire light emitting diodes probed by electron beam induced current microscopy. <i>Nanotechnology</i> , 2014 , 25, 255201	3.4	30
7	Metal organic vapour-phase epitaxy growth of GaN wires on Si (111) for light-emitting diode applications. <i>Nanoscale Research Letters</i> , 2013 , 8, 61	5	25
6	Self-organized and self-catalyst growth of semiconductor and metal wires by vapour phase epitaxy: GaN rods versus Cu whiskers. <i>Comptes Rendus Physique</i> , 2013 , 14, 221-227	1.4	11
5	Single-Wire Light-Emitting Diodes Based on GaN Wires Containing Both Polar and Nonpolar InGaN/GaN Quantum Wells. <i>Applied Physics Express</i> , 2012 , 5, 014101	2.4	54
4	M-plane core-shell InGaN/GaN multiple-quantum-wells on GaN wires for electroluminescent devices. <i>Nano Letters</i> , 2011 , 11, 4839-45	11.5	172
3	Light emitting diodes based on GaN core/shell wires grown by MOVPE on n-type Si substrate. <i>Electronics Letters</i> , 2011 , 47, 765-767	1.1	47
2	Self-assembled growth of catalyst-free GaN wires by metal-organic vapour phase epitaxy. <i>Nanotechnology</i> , 2010 , 21, 015602	3.4	167
1	Homoepitaxial growth of catalyst-free GaN wires on N-polar substrates. <i>Applied Physics Letters</i> , 2010 , 97, 151909	3.4	108